### (12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

# (19) World Intellectual Property Organization International Bureau



### 

(43) International Publication Date 23 June 2005 (23.06.2005)

**PCT** 

## (10) International Publication Number WO 2005/057638 A1

(51) International Patent Classification<sup>7</sup>: 21/266

H01L 21/18,

(21) International Application Number:

PCT/GB2004/004944

(22) International Filing Date:

24 November 2004 (24.11.2004)

(25) Filing Language:

English

(26) Publication Language:

English

(30) Priority Data:

0328808.1

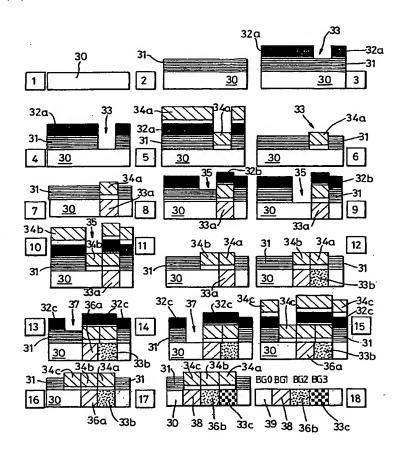
10 December 2003 (10.12.2003) GB

(71) Applicant (for all designated States except US): IN-TENSE LIMITED [GB/GB]; 4 Stanley Boulevard, Hamilton International Technology Park, High Blantyre, Glassgow G72 0BN (GB).

- (72) Inventors; and
- (75) Inventors/Applicants (for US only): MARSH, John, Haig [GB/GB]; 1 Bellshaugh Gardens, Glasgow G12 OSN (GB). YANSON, Dan Andreyevitch [RU/GB]; 52 Springhill Gardens, Glasgow G41 2EY (GB). Mc-DOUGALL, Stewart, Duncan [GB/GB]; Bethany Cottage, 1 Hazelbank Braes, Hazelbank, Lanark ML11 9XL (GB).
- (74) Agent: CHARIG, Raymond; Eric Potter Clarkson, Park View House, 58 The Ropewalk, Nottingham NG1 5DD (GB).
- (81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG,

[Continued on next page]

### (54) Title: MULTIPLE ANNEAL INDUCED DISORDERING



(57) Abstract: A quantum well intermixing (QWI) technique for modifying an energy bandgap during the formation of optical semiconductor devices enables spatial control of the QWI process so as to achieve differing bandgap shifts across a wafer, device or substrate surface. The method includes: patterning the surface of a semiconductor substrate with QW1-initiating material in first regions of the surface; conducting a first thermal processing cycle on the substrate to generate a first bandgap shift in the first regions; patterning the surface of the substrate with QWI-initiating material in second regions of the surface, distinct from said first regions; and conducting a second thermal processing cycle on the substrate to generate a second bandgap shift in the second regions, and to generate a cumulative bandgap shift in the first regions, the cumulative bandgap shift being the cumulative result of said first and second thermal processing cycles. Further steps can produce additional cumulative bandgap shifts.

### WO 2005/057638 A1



PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LU, MC, NL, PL, PT, RO, SE,

SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

#### Published:

with international search report

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.